TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSII<sup>.5</sup>)

# 2SK1930

Chopper Regulator, DC-DC Converter, and Motor Drive Applications

• Low drain–source ON resistance : RDS (ON) = 3.0  $\Omega$  (typ.)

• High forward transfer admittance  $: |Y_{fs}| = 2.0 \text{ S (typ.)}$ 

• Low leakage current  $: I_{DSS} = 300 \mu A \text{ (max) (V}_{DS} = 800 \text{ V)}$ 

• Enhancement mode :  $V_{th} = 1.5 \sim 3.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$ 

#### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                              |                | Symbol           | Rating  | Unit                |
|--|----------------|------------------|---------|---------------------|
| Drain-source voltage                         |                | $V_{DSS}$        | 1000    | $\langle v \rangle$ |
| Drain-gate voltage (R <sub>GS</sub> = 20 kΩ) |                | $V_{DGR}$        | 1000    | V                   |
| Gate-source voltage                          |                | $V_{GSS}$        | ±20     | V                   |
| Drain current                                | DC (Note 1)    | I <sub>D</sub>   | 4       | A                   |
|  | Pulse (Note 1) | $I_{DP}$         | 12      |                     |
| Drain power dissipation (Tc = 25°C)          |                | PD               | 100     | W                   |
| Channel temperature                          |                | T <sub>ch</sub>  | 150     | ⟨⟨c                 |
| Storage temperature range                    |                | T <sub>stg</sub> | -55~150 | °C                  |

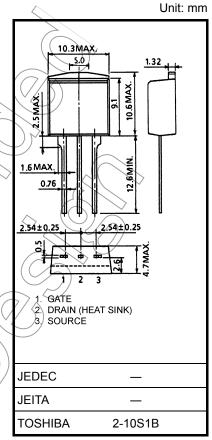
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

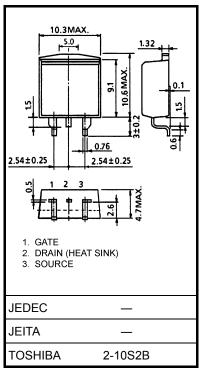
| Characteristics                        | Symbol     | Max  | Unit |
|--|------------|------|------|
| Thermal resistance, channel to case    | Rth (ch-c) | 1.25 | °C/W |
| Thermal resistance, channel to ambient | Rth (eh-a) | 83.3 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



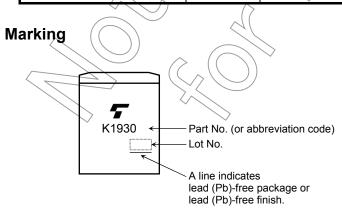
Weight: 1.5 g (typ.)

#### **Electrical Characteristics (Ta = 25°C)**

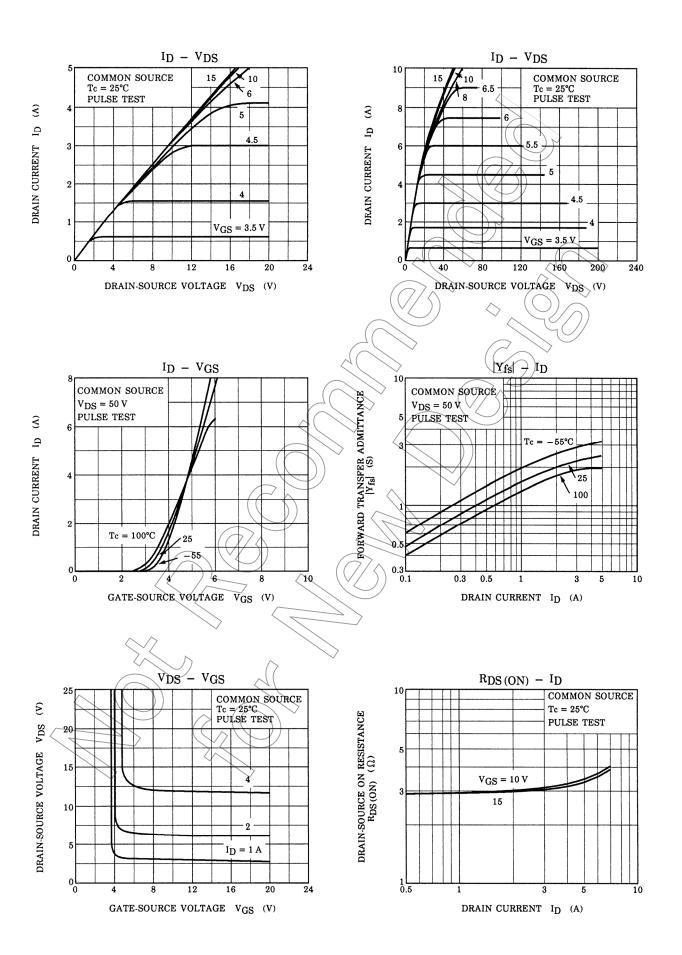
| Charac                               | cteristics    | Symbol               | Test Condition   | Min   | Тур. | Max  | Unit |
|--------------------------------------|---------------|----------------------|--|---|------|------|------|
| Gate leakage cu                      | ırrent        | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V                             | _   | _    | ±100 | nA   |
| Drain cut-off cui                    | rrent         | I <sub>DSS</sub>     | V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V                             | _   | _    | 300  | μA   |
| Drain-source br<br>voltage           | eakdown       | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                              | 1000  | _    | _    | V    |
| Gate threshold v                     | voltage       | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                              | (1.5  | 7    | 3.5  | V    |
| Drain-source Ol                      | N resistance  | R <sub>DS (ON)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A                               |   | 3.0  | 3.8  | Ω    |
| Forward transfer                     | r admittance  | Y <sub>fs</sub>      | V <sub>DS</sub> = 20 V, I <sub>D</sub> = 2 A                               | 1.0   | 2.0  | 1    | S    |
| Input capacitano                     | e             | C <sub>iss</sub>     |  |   | 700  |      |      |
| Reverse transfer                     | r capacitance | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz                   | · —   | 55   | -    | pF   |
| Output capacitance                   |               | Coss                 |  | _   | 100  |      |      |
| Switching time                       | Rise time     | t <sub>r</sub>       | V <sub>GS</sub> 10V I <sub>D</sub> =2A V <sub>OUT</sub>                    | -   | 18   | //   |      |
|                                      | Turn-on time  | t <sub>on</sub>      | $R_{L} = 200\Omega$  |   | 30   | ) –  | - ns |
|                                      | Fall time     | t <sub>f</sub>       | V <sub>DD</sub> ≒400V  | \<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\<br>\ | 12   |      |      |
|                                      | Turn-off time | t <sub>off</sub>     | Duty $\leq 1\%$ , $t_{\rm W} = 10 \mu \rm s$                               |   | 70   | 1    |      |
| Total gate charg<br>plus gate-drain) |               | Qg                   |  |   | 60   |      |      |
| Gate-source charge                   |               | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 4 \text{ A}$ |   | 35   | _    | nC   |
| Gate-drain ("miller") charge         |               | Q <sub>gd</sub>      |  |   | 25   |      |      |

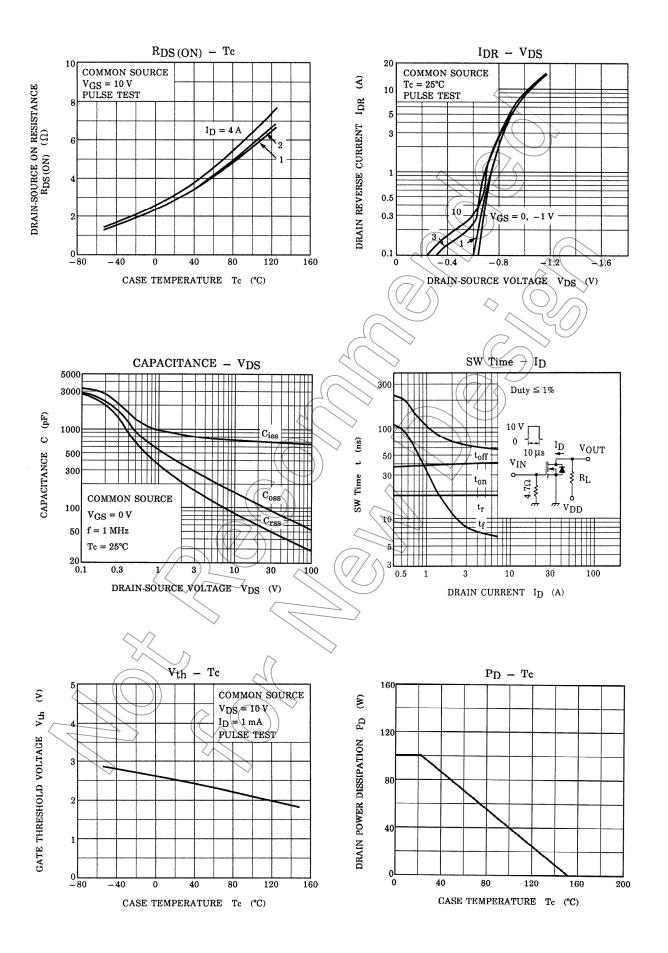
## Source-Drain Ratings and Characteristics (Ta = 25°C)

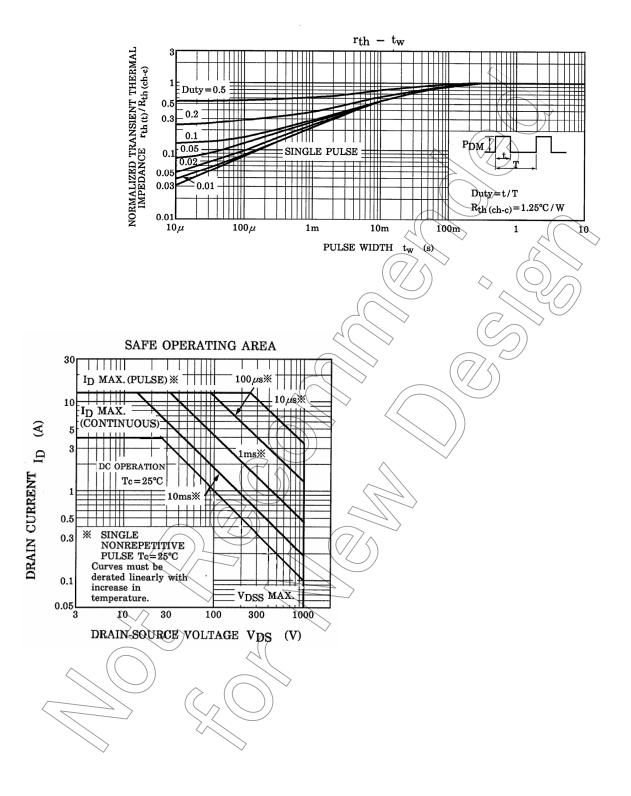
|   |                    | A 11 4                                       |     |      |      |      |
|---|--------------------|--|-----|------|------|------|
| Characteristics                           | Symbol             | Test Condition                               | Min | Тур. | Max  | Unit |
| Continuous drain reverse current (Note 1) | JÓR                | <u> </u>                                     | -   | _    | 4    | Α    |
| Pulse drain reverse current (Note 1)      | \ I <sub>DRP</sub> | _  |     |      | 12   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub>   | I <sub>DR</sub> = 4 A, V <sub>GS</sub> = 0 V | _   | _    | -1.9 | V    |



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